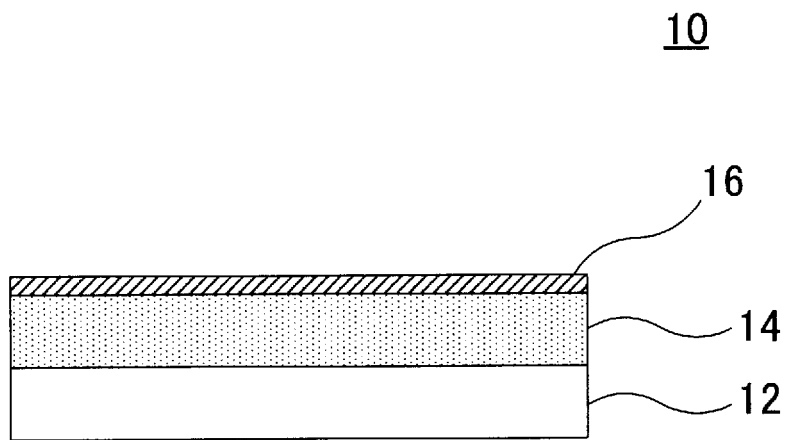
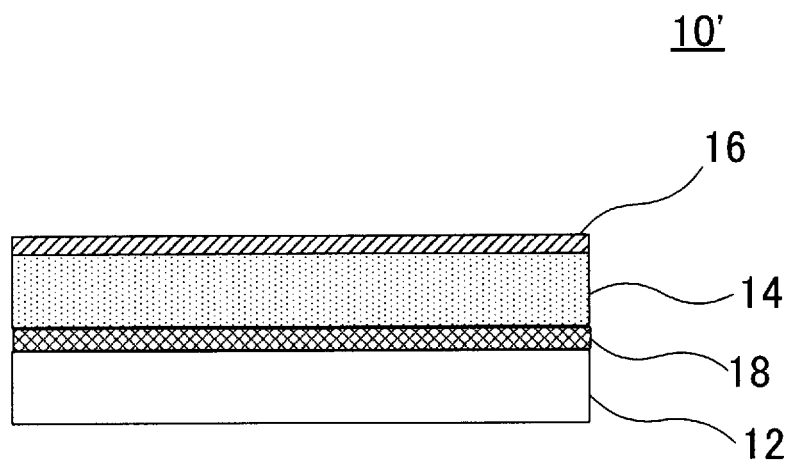


[図1A]



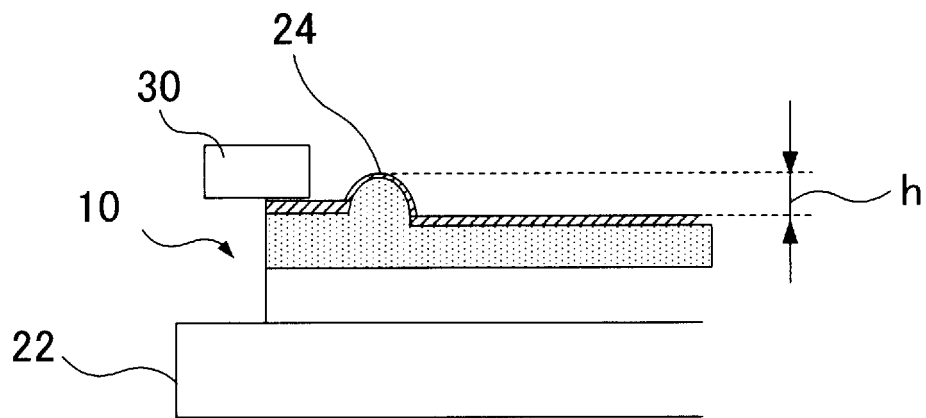
[図1B]



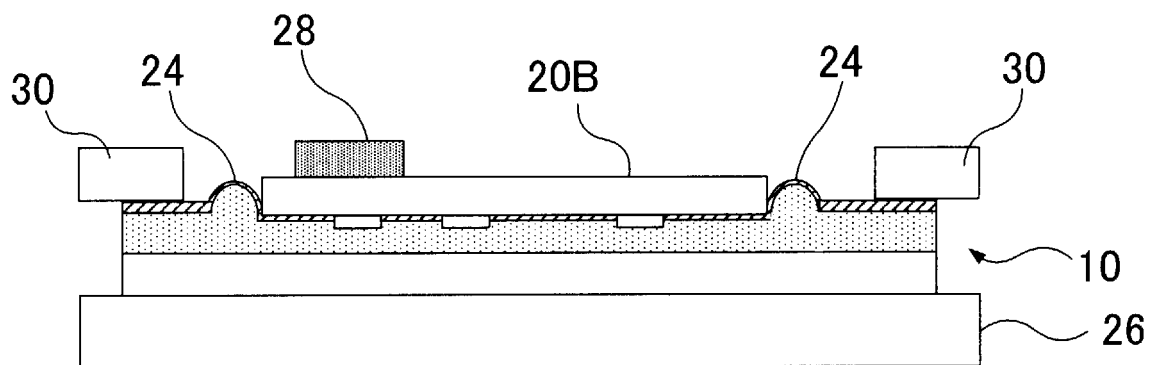
A cross-sectional view of a semiconductor device 10. The device consists of a substrate 40 with a base layer 30. On top of the base layer 30 is a stack of layers: a bottom layer 16 (hatched), a middle layer 14 (dotted), and a top layer 12 (white). A circular feature 35 with a '+' sign is positioned above the top layer 12. An arrow points from the circular feature 35 towards the right, indicating a direction of process or assembly. The top layer 12 is labeled with 20 and 20A.

A cross-sectional view of a semiconductor device 10. The device consists of a substrate 22-2, a first insulating layer 22-1, and a second insulating layer 24. A conductive layer 20 is formed on the first insulating layer 22-1. The conductive layer 20 is divided into a central portion and two side portions. The side portions are connected to the substrate 22-2 by vias 30. The top surface of the central portion of the conductive layer 20 is covered by a protective layer 24.

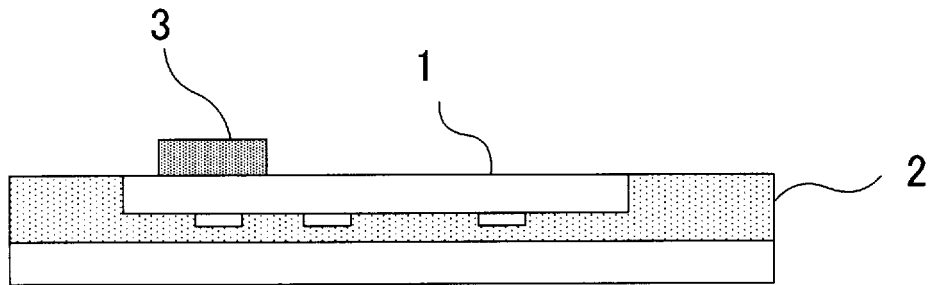
[図2D]



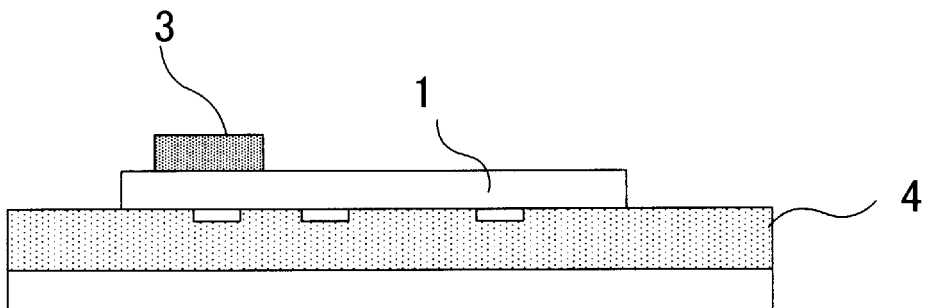
[図2E]



[図3]



[図4]



[図5]

図5A

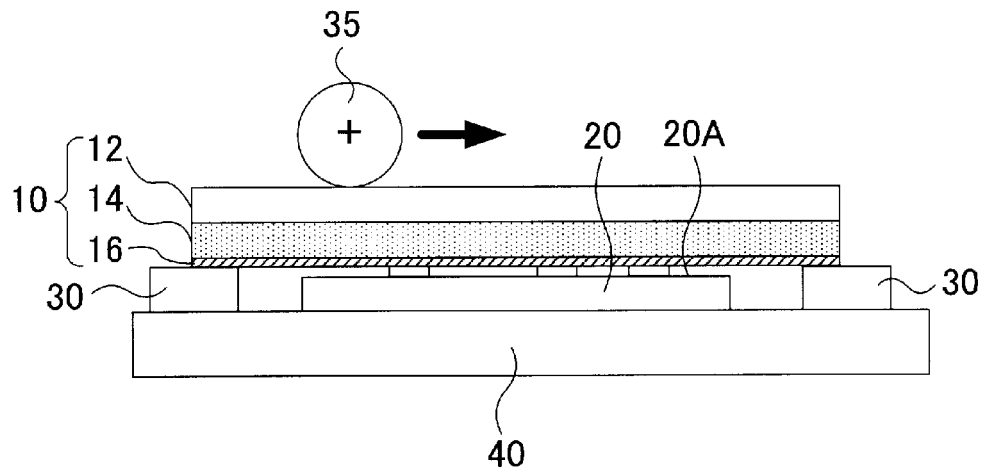
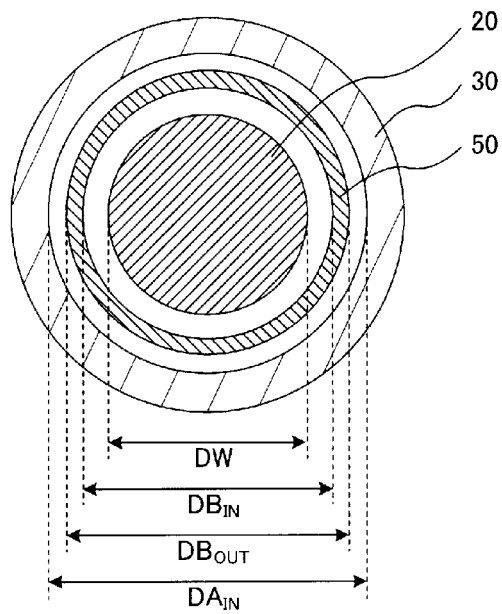
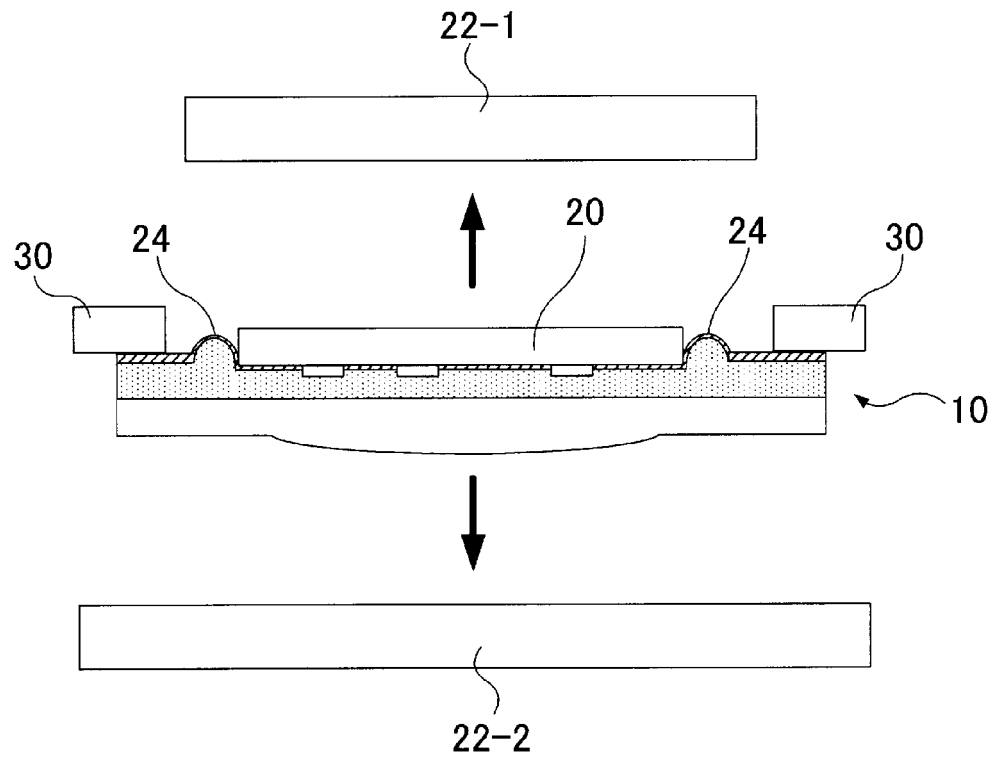


図5B



[図6]



[図7]

図7A

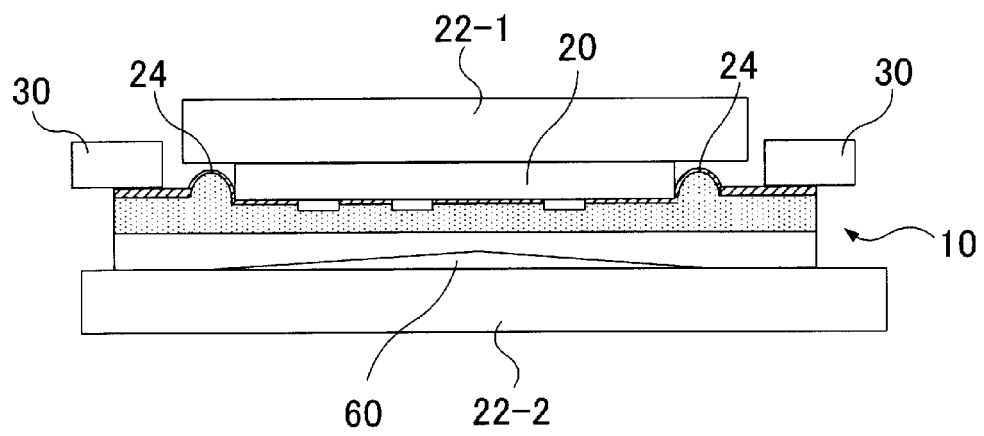


図7B

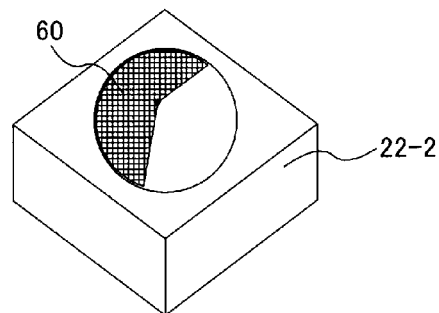
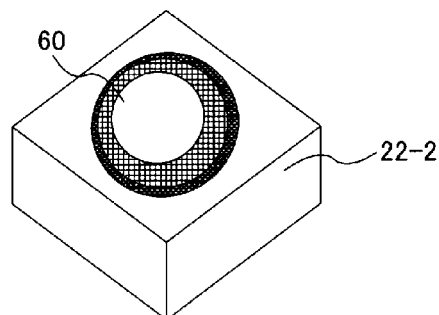


図7C



[図8]

図8A

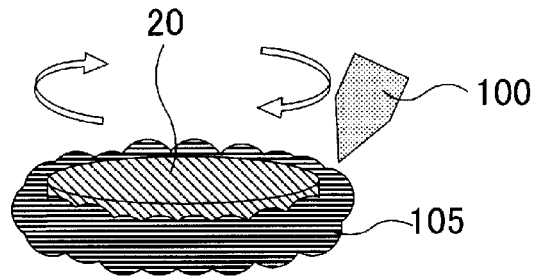


図8B

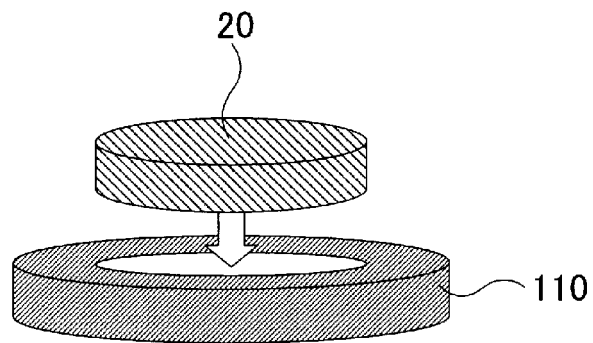


図8C

